

PSMN1R2-30YLC

N-channel 30 V 1.25m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 3 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	215	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R _{DSon} drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12		-	1.35	1.65	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12		-	1.05	1.25	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see Figure 15	-	11.6	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; see Figure 14; see Figure 15	-	38	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN1R2-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PSMN1R2-30YLC	1C230L

[1] % = placeholder for manufacturing site code

PSMN1R2-30YLC

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5. Limiting values

Table 5. Limiting values

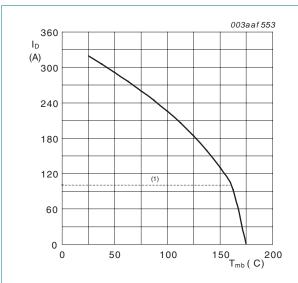
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4		-	1237	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	215	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		900	-	V
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1237	Α
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped; see Figure 3		-	209	mJ

^[1] Continuous current is limited by package.

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N-channel 30 V 1.25mΩ logic level MOSFET in LFPAK using NextPower



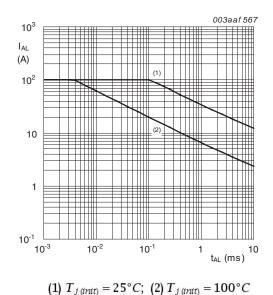
 $V_{GS} \ge 10V$; (1) Capped at 100A due to package

120 P_{der} (%) 80 40 0 _ 100 150 200 T_{mb} (°C)

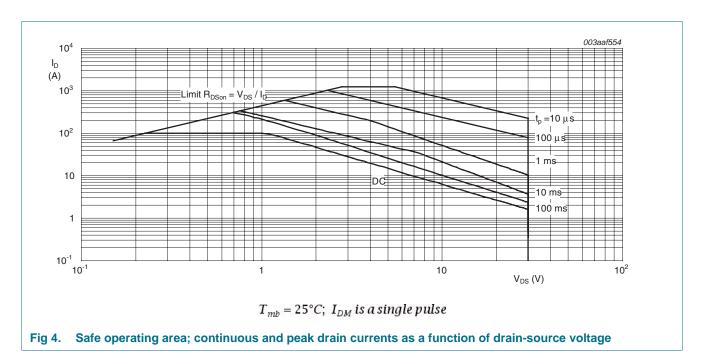
 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Continuous drain current as a function of mounting base temperature

Normalized total power dissipation as a Fig 2. function of mounting base temperature



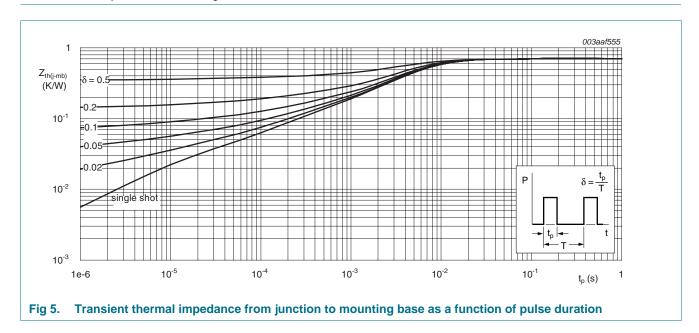
Single pulse avalanche rating; avalanche current as a function of avalanche time Fig 3.



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	0.58	0.7	K/W



7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.46	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon} drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 12</u>	-	1.35	1.65	mΩ	
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 °C;$ see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	2.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	1.05	1.25	mΩ
		$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $T_j = 150 \text{ °C}$; see Figure 13; see Figure 12	-	-	2.05	mΩ
R_G	gate resistance	f = 1 MHz	-	1.1	2.2	Ω
Dynamic ch	naracteristics					
$Q_{G(tot)}$ total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	78	-	nC	
		$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 14; see Figure 15	-	38	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	75	-	nC
Q _{GS}	gate-source charge	1 05 1 1 45 1 45 1				nC
_	gate course charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$;	-	10.3	-	IIC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 15	-	10.3 6.7	-	nC
Q _{GS(th)}	pre-threshold		-			
Q _{GS(th-pl)}	pre-threshold gate-source charge post-threshold		-	6.7	-	nC
Q _{GS(th-pl)}	pre-threshold gate-source charge post-threshold gate-source charge		- - - -	6.7 3.6	-	nC nC
$Q_{GS(th\text{-}pl)}$ Q_{GD} $V_{GS(pl)}$	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau	see Figure 14; see Figure 15 $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \underline{\text{Figure 14}};$	- - - -	6.7 3.6 11.6	-	nC nC
$Q_{GS(th\text{-}pl)}$ Q_{GD} $V_{GS(pl)}$	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage	see <u>Figure 14</u> ; see <u>Figure 15</u> $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \underline{\text{Figure 14}}; \text{ see } \underline{\text{Figure 15}}$	- - - - -	6.7 3.6 11.6 2.34		nC nC nC
Q _{GS(th-pl)} Q _{GD} V _{GS(pl)} C _{iss} C _{oss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance	see Figure 14; see Figure 15 $I_D = 25 \text{ A; } V_{DS} = 15 \text{ V; see } \underline{\text{Figure 14;}}$ see Figure 15 $V_{DS} = 15 \text{ V; } V_{GS} = 0 \text{ V; } f = 1 \text{ MHz;}$	- - - - - - -	6.7 3.6 11.6 2.34 5093		nC nC nC V
$Q_{GS(th ext{-pl})}$ Q_{GD} $V_{GS(pl)}$ C_{iss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer	see Figure 14; see Figure 15 $I_D = 25 \text{ A; } V_{DS} = 15 \text{ V; see } \underline{\text{Figure 14;}}$ see Figure 15 $V_{DS} = 15 \text{ V; } V_{GS} = 0 \text{ V; } f = 1 \text{ MHz;}$	- - - - - -	6.7 3.6 11.6 2.34 5093 977	- - - -	nC nC v pF pF
Q _{GS(th-pl)} Q _{GD} V _{GS(pl)} C _{iss} C _{oss} C _{rss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance	see Figure 14; see Figure 15 $I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; see Figure 14; see Figure 15 $V_{DS} = 15 \text{ V}$; $V_{GS} = 0 \text{ V}$; $V_{GS} = 10 \text{ MHz}$; $V_{DS} = 15 \text{ V}$; see Figure 16	- - - - - - -	6.7 3.6 11.6 2.34 5093 977 333	- - - - -	nC nC V pF pF pF
$\begin{array}{c} Q_{GS(\text{th-pl})} \\ \\ Q_{GD} \\ \\ V_{GS(\text{pl})} \\ \\ C_{iss} \\ \\ C_{oss} \\ \\ C_{rss} \\ \\ t_{d(on)} \end{array}$	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance turn-on delay time	see Figure 14; see Figure 15 $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see Figure 14};$ see Figure 15 $V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see Figure 16}$ $V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	- - - - - - - -	6.7 3.6 11.6 2.34 5093 977 333 36	- - - - -	nC nC V pF pF pF ns

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 Table 7.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 ^{\circ}\text{C}$	-	33	-	nC
Source-drain	diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	41.5	-	ns
Q _r	recovered charge	V _{DS} = 15 V	-	45	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 15 \text{ V; see } \frac{\text{Figure } 18}{\text{Im}}$	-	25	-	ns
t _b	reverse recovery fall time		-	16.5	-	ns

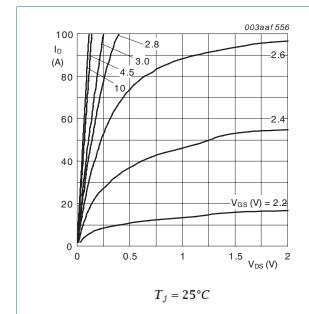


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

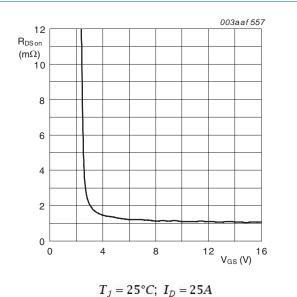
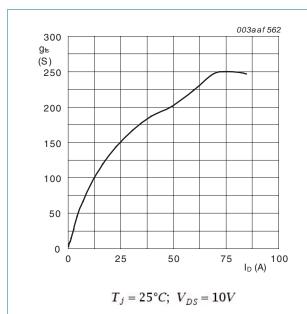


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



Forward transconductance as a function of Fig 8. drain current; typical values

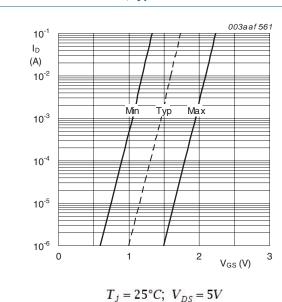
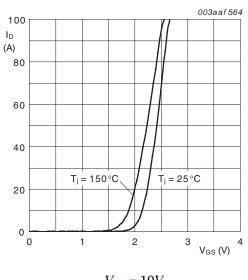


Fig 10. Sub-threshold drain current as a function of gate-source voltage



 $V_{DS} = 10V$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage

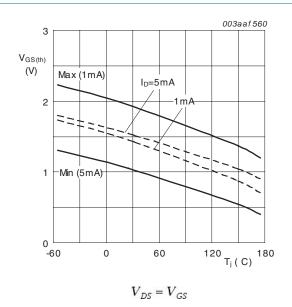


Fig 11. Gate-source threshold voltage as a function of junction temperature

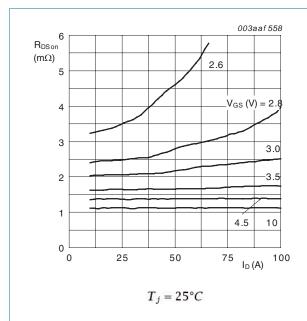


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

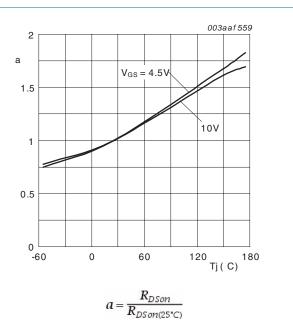


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

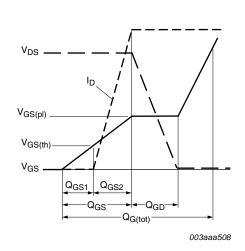


Fig 14. Gate charge waveform definitions

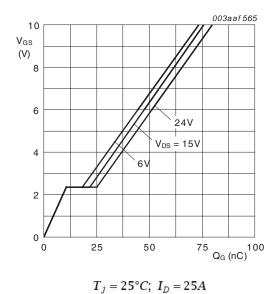


Fig 15. Gate-source voltage as a function of gate charge; typical values

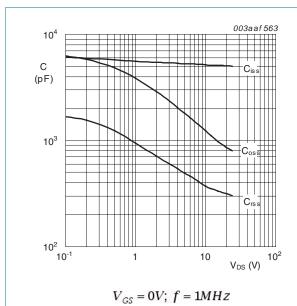


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

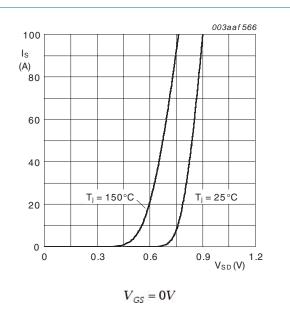


Fig 17. Source current as a function of drain-source voltage; typical values

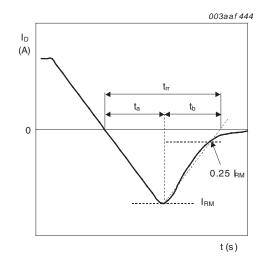


Fig 18. Reverse recovery timing definition

Package outline

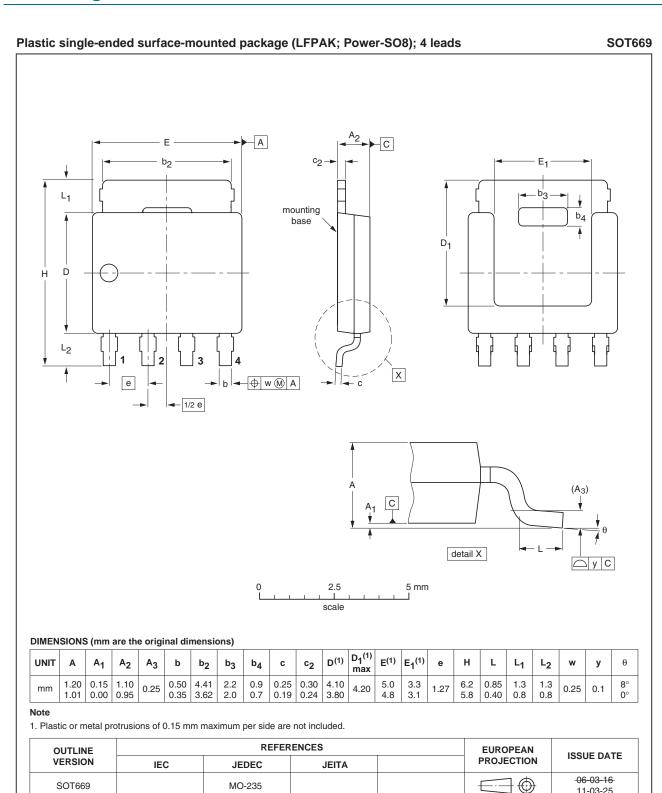


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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11-03-25

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R2-30YLC v.1	20110503	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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PSMN1R2-30YLC

N-channel 30 V 1.25mΩ logic level MOSFET in LFPAK using NextPower

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12. Contents

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